

Supporting Information

Highly Conductive Tungsten Doped Tin(IV) Oxide Transparent Electrodes Delivered by Lattice-Strain Control

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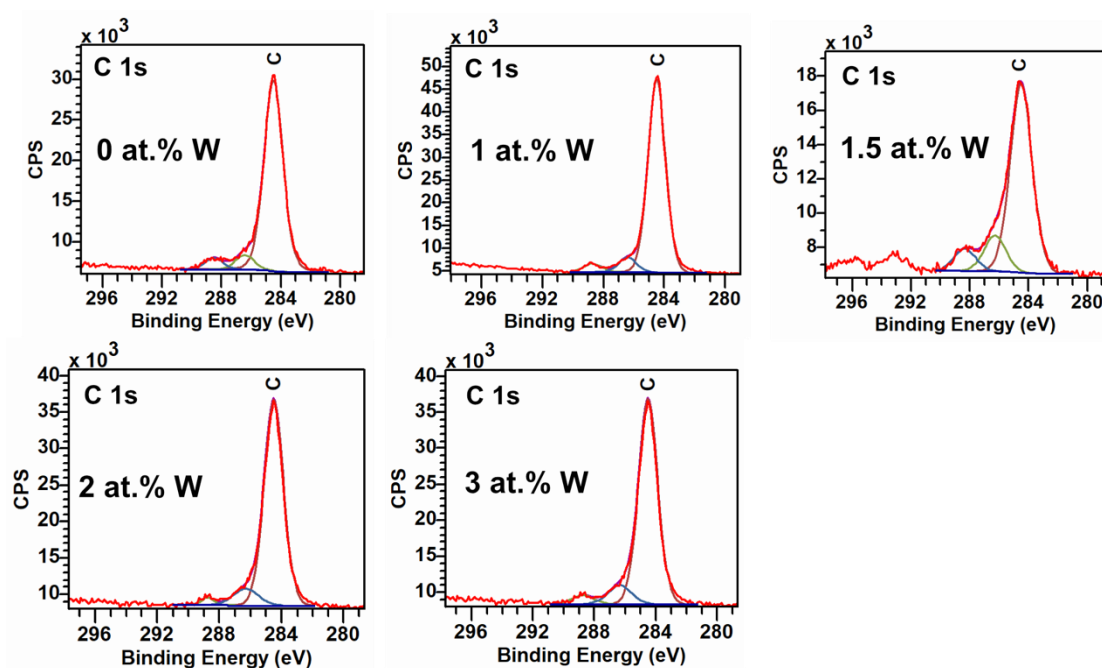


Figure S1: Carbon 1s XPS data used for the 0-3 at.% W:SnO₂ films grown on glass via CVD. The principle C1s peak for aliphatic C/adventitious carbon was used for charge correction (284.5 eV)

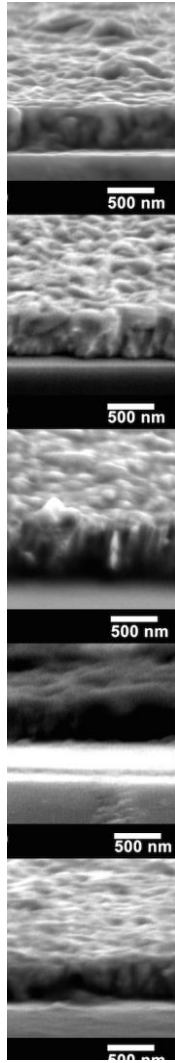


Figure S2: Side on SEM images for (top to bottom) 0,1, 1.5,2,3 at.% W : SnO₂ films showing film thickness of 500, 500, 520, 500, 540 nm, respectively.